

## SOT-323 Plastic-Encapsulated Diode

### BAW56W SWITCHING DIODE

#### FEATURES

Power dissipation

$P_D$ : 200 mW (Tamb=25°C)

Collector current

$I_O$ : 150 mA

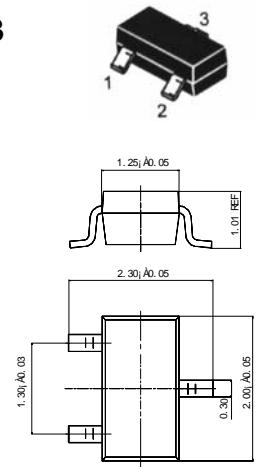
Collector-base voltage

$V_R$ : 75 V

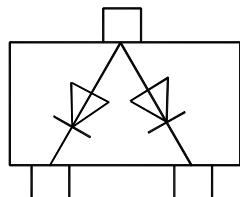
Operating and storage junction temperature range

$T_J, T_{stg}$ : -55°C to +150°C

**SOT-323**



Unit: mm



Marking: KJC

#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R = 100\mu A$	75		V
Reverse voltage leakage current	$I_R$	$V_R = 75V$		2.5	$\mu A$
Forward voltage	$V_F$	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$		715 855 1000 1250	mV
Diode capacitance	$C_D$	$V_R = 0V, f = 1MHz$		2	pF
Reveres recovery time	$t_{rr}$	$I_F = I_R = 10mA$ $I_{rr} = 0.1 \times I_R$		4	nS